# XN04211 (XN4211)

## Silicon NPN epitaxial planar type

For switching/digital circuits

#### Features

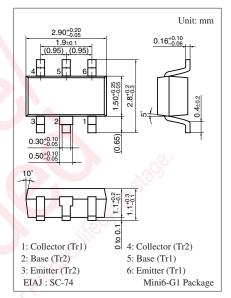
- Two elements incorporated into one package (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

#### Basic Part Number

• UNR2211 (UN2211) × 2

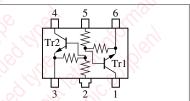
#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol Rating		Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V	
Collector current	I <sub>C</sub>	100	mA	
Total power dissipation	P <sub>T</sub>	300	mW	
Junction temperature	Тј	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



#### Marking Symbol: 9V

#### Internal Connection



### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

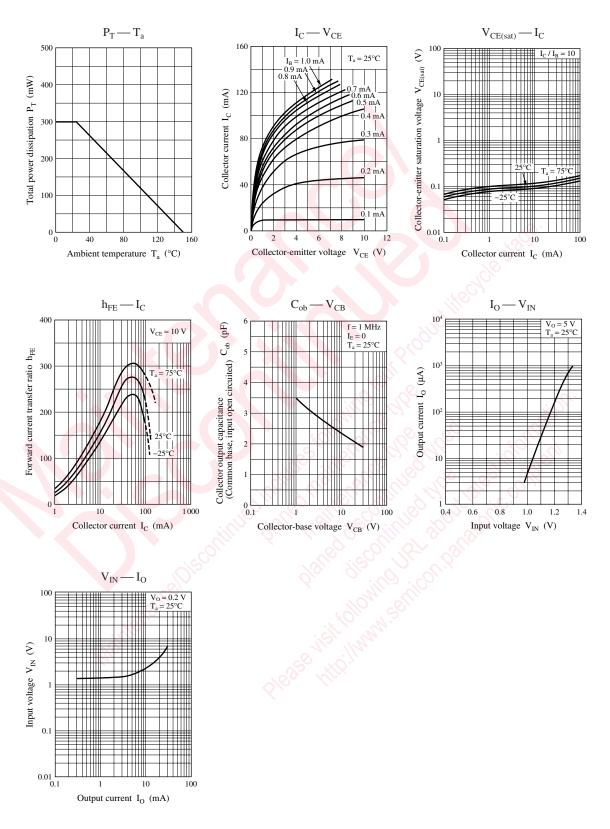
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 6 V, I_C = 0$			0.5	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	35			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.3 \text{ mA}$			0.25	V
Output voltage high-level	V <sub>OH</sub>	$V_{CC} = 5 \text{ V}, \text{ V}_{B} = 0.5 \text{ V}, \text{ R}_{L} = 1 \text{ k}\Omega$	4.9			V
Output voltage low-level	V <sub>OL</sub>	$V_{CC} = 5 \text{ V},  \text{V}_{B} = 2.5  \text{V},  \text{R}_{L} = 1  \text{k}\Omega$			0.2	V
Input resistance	R <sub>1</sub>		-30%	10	+30%	kΩ
Resistance ratio	R <sub>1</sub> / R <sub>2</sub>		0.8	1.0	1.2	
Transition frequency	f <sub>T</sub>	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Note) The part number in the parenthesis shows conventional part number.

## XN04211





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